## (19) World Intellectual Property Organization

International Bureau





(43) International Publication Date 1 September 2005 (01.09.2005)

## (10) International Publication Number WO 2005/081323 A3

- (51) International Patent Classification<sup>7</sup>: H01L 29/78, 29/10, 21/336, 29/78, 29/10, 21/336, 29/423 // 29/739, 21/331
- (21) International Application Number:

PCT/IB2005/050595

(22) International Filing Date:

17 February 2005 (17.02.2005)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

0403934.3

21 February 2004 (21.02.2004)

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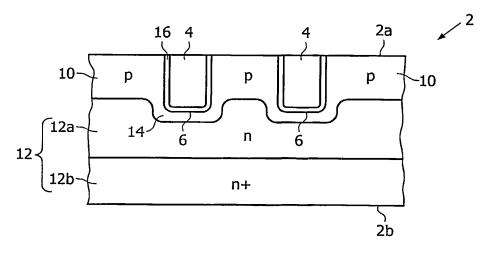
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- (81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.
- (84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

## Published:

- with international search report
- (88) Date of publication of the international search report: 23 February 2006

[Continued on next page]

(54) Title: TRENCH-GATE SEMICONDUCTOR DEVICES AND THE MANUFACTURE THEREOF



(57) Abstract: A vertical trench-gate semiconductor device wherein the trench-gates extend in stripes, the source regions extend transversely between the trenchgates in stripes, projection (20) of the source stripes across the trench-gates defines intermediate trench portions (22) between the projected source stripes, and mutually spaced regions (14,14) of the second conductivity type are to provided immediately below the intermediate trench portions (22) which are connected to source potential. The spaced regions serve to selectively shield portions of the trench-gate from the drain region to suppress their contribution to Cgd and hence Qgd. In particular, they shield those portions of the trenchgate which do not contribute to the channel width of the device, without restricting the current path where a channel is formed.





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For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.